

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	I_D $T_A = +25^\circ\text{C}$
-20V	65mΩ @ $V_{GS} = -4.5\text{V}$	-4.2A
	100mΩ @ $V_{GS} = -2.5\text{V}$	-3.4A

Description

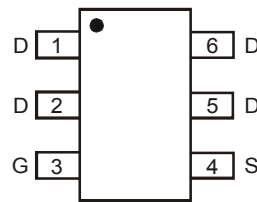
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

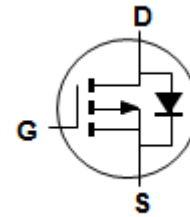
- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control



Top View



Top View
Pin-Out



Internal Schematic

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

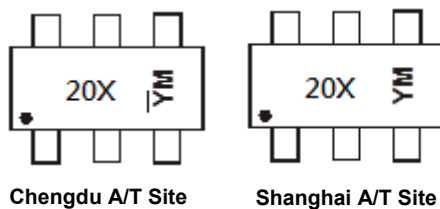
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – MatteTin annealed over Copper leadframe.
Solderable per MIL-STD-202, Method 208 E3
- Weight: 0.0013 grams (approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2033UVT-7	TSOT26	3000/Tape & Reel
DMP2033UVT -13	TSOT26	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Chengdu A/T Site

Shanghai A/T Site

20X = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or ∇ = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Drain Current (Note 6)	Steady State	$T_A = +25^\circ\text{C}$	I_D	-4.2	A
		$T_A = +70^\circ\text{C}$		-3.4	
Pulsed Drain Current (Note 6)			I_{DM}	-10	A

Thermal Characteristics

Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)			P_D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)		Steady State	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)			P_D	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)		Steady State	$R_{\theta JA}$	74	$^\circ\text{C/W}$
Operating and Storage Temperature Range			T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	μA	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$ $T_J = +25^\circ\text{C}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	—	-0.9	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	45	65	m Ω	$V_{GS} = -4.5\text{V}, I_D = -4.2\text{A}$
			57	100		$V_{GS} = -2.5\text{V}, I_D = -3.4\text{A}$
			80	200		$V_{GS} = -1.8\text{V}, I_D = -2\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	—	9	—	S	$V_{DS} = -5\text{V}, I_D = -4\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	845	—	pF	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	72	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	63	—	pF	
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q_g	—	10.4	—	nC	$V_{GS} = -4.5\text{V}, V_{DS} = -4\text{V},$ $I_D = -3.5\text{A}$
Gate-Source Charge	Q_{gs}	—	1.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.9	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	6.5	—	ns	$V_{DS} = -4\text{V}, V_{GS} = -4.5\text{V},$ $R_G = 6\Omega, I_D = -1\text{A}$
Turn-On Rise Time	t_r	—	13.4	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	51.5	—	ns	
Turn-Off Fall Time	t_f	—	21.8	—	ns	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

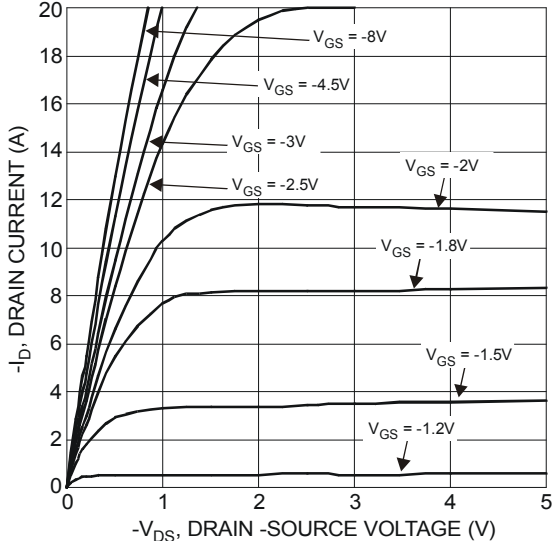


Figure 1 Typical Output Characteristics

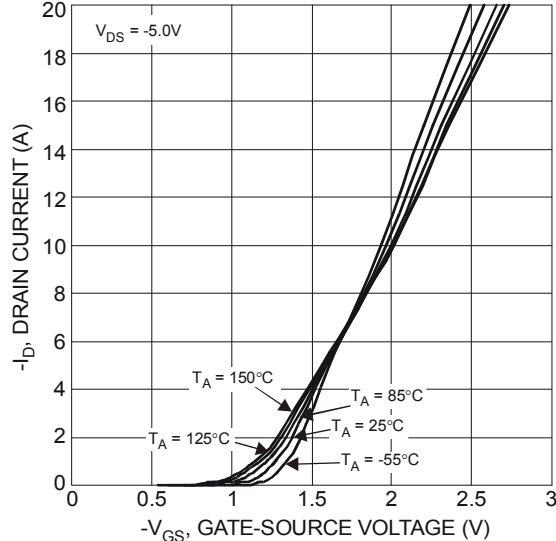


Figure 2 Typical Transfer Characteristics

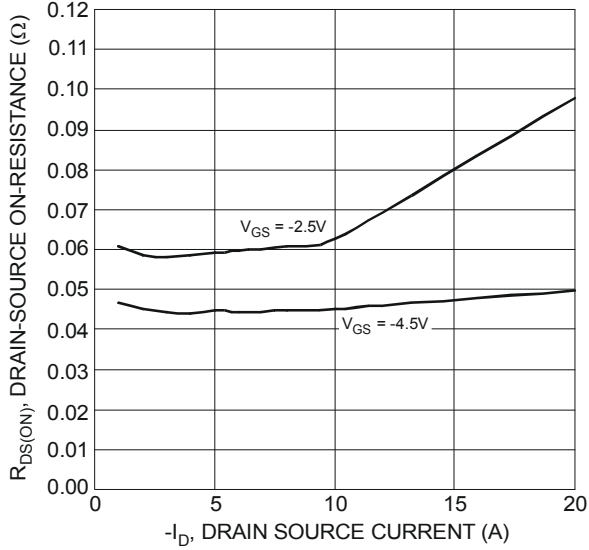


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

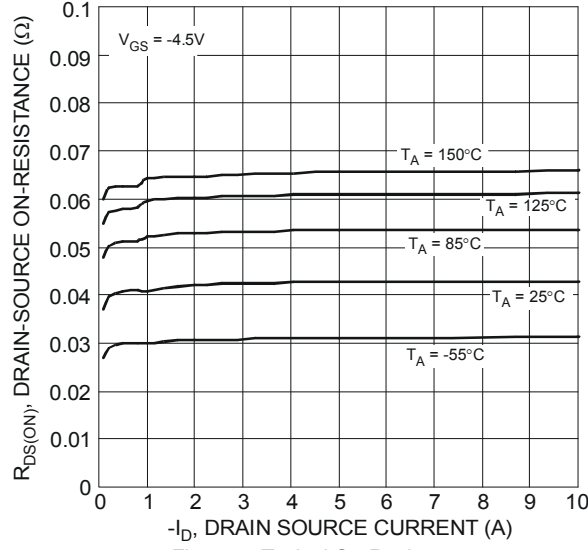


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

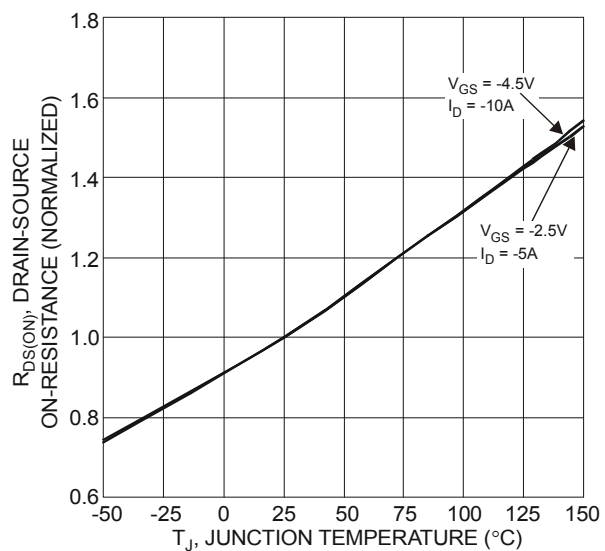


Figure 5 On-Resistance Variation with Temperature

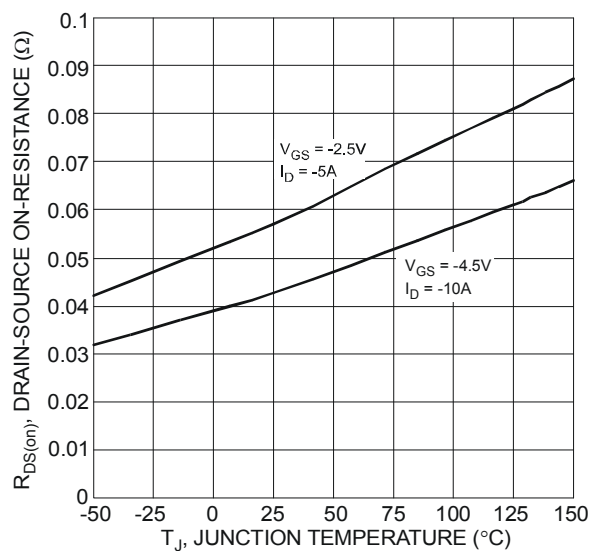


Figure 6 On-Resistance Variation with Temperature

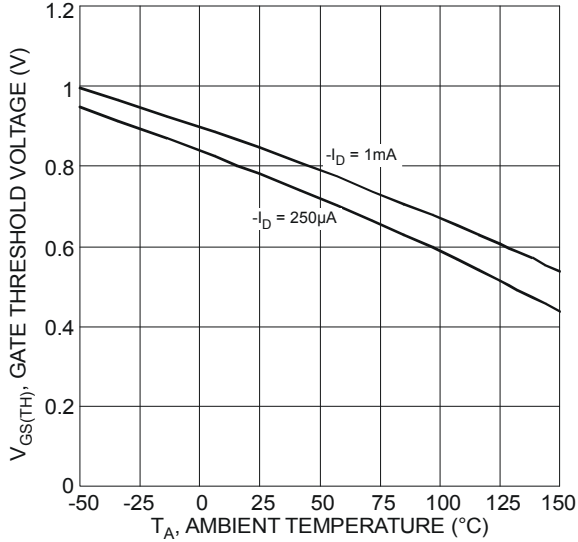


Figure 7 Gate Threshold Variation vs. Ambient Temperature

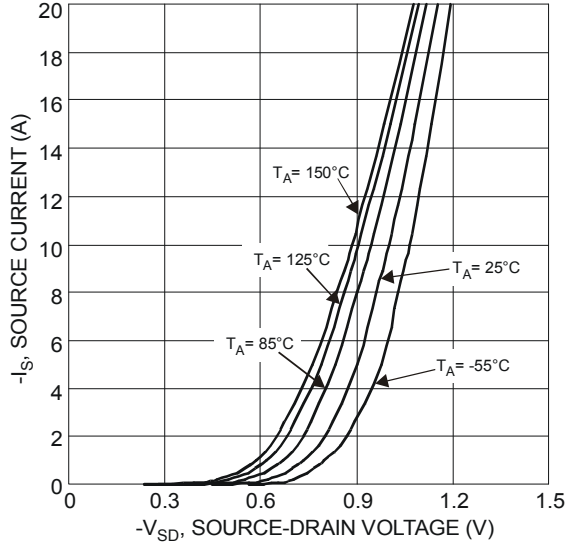


Figure 8 Diode Forward Voltage vs. Current

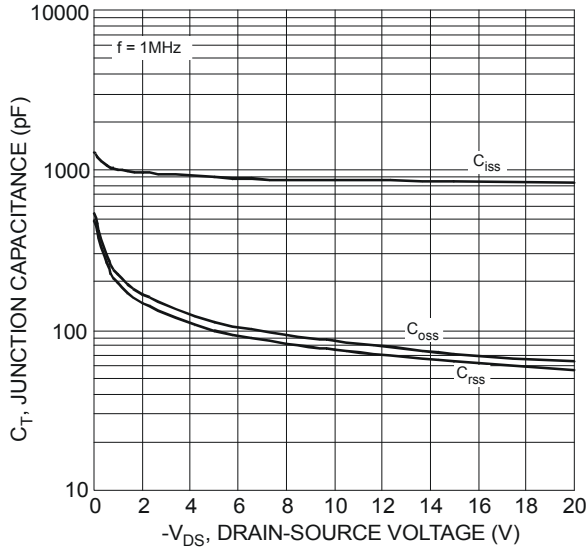


Figure 9 Typical Junction Capacitance

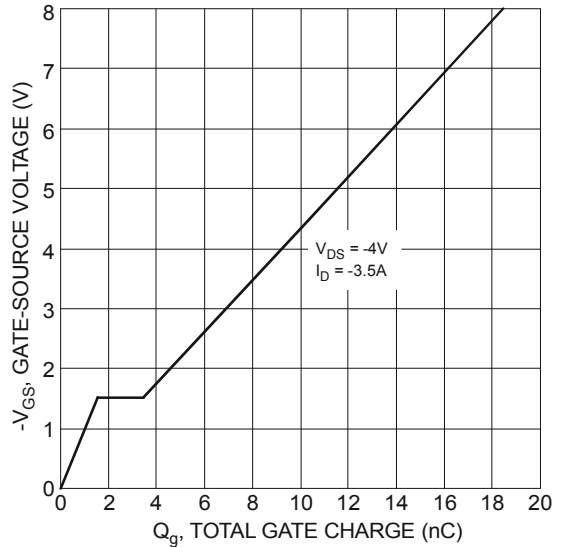
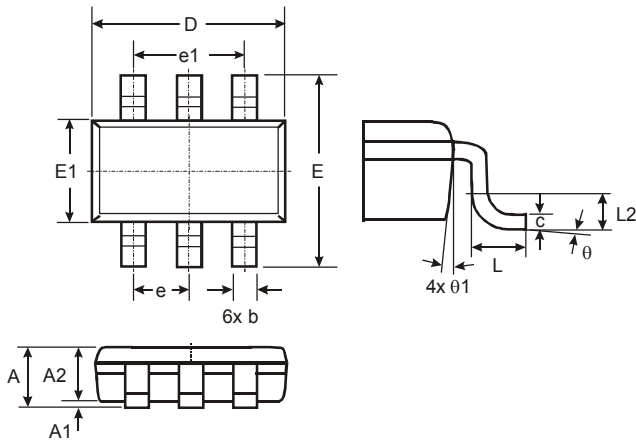


Figure 10 Gate-Charge Characteristics

Package Outline Dimensions

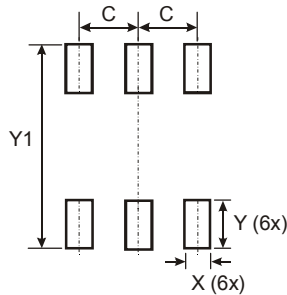
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TSOT26			
Dim	Min	Max	Typ
A	-	1.00	-
A1	0.01	0.10	-
A2	0.84	0.90	-
D	-	-	2.90
E	-	-	2.80
E1	-	-	1.60
b	0.30	0.45	-
c	0.12	0.20	-
e	-	-	0.95
e1	-	-	1.90
L	0.30	0.50	-
L2	-	-	0.25
θ	0°	8°	4°
θ1	4°	12°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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